

R07DS0323EJ0600

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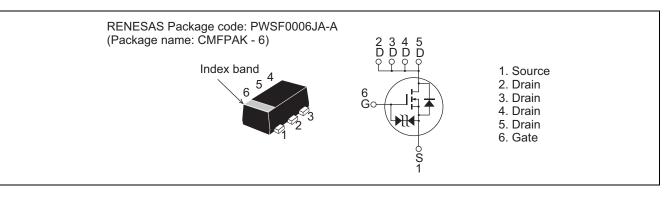
HAT2203C

Silicon N Channel MOS FET Power Switching

Features

- Low on-resistance
- $R_{DS(on)} = 69 \text{ m}\Omega \text{ typ.}(\text{at } V_{GS} = 4.5 \text{ V})$
- Low drive current
- High density mounting
- 2.5 V gate drive device

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

		-	(1u = 25 C)
Item	Symbol	Ratings	Unit
Drain to Source voltage	V _{DSS}	20	V
Gate to Source voltage	V _{GSS}	±12	V
Drain current	ID	2	А
Drain peak current	I _{D (pulse)} Note1	8	А
Body - Drain diode reverse Drain current	I _{DR}	2	А
Channel dissipation	Pch ^{Note2}	830	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	۵°

Notes: 1. $PW \leq 10 \ \mu s, \ duty \ cycle \leq 1\%$

2. When using the glass epoxy board (FR4 40 x 40 x 1.6mm)



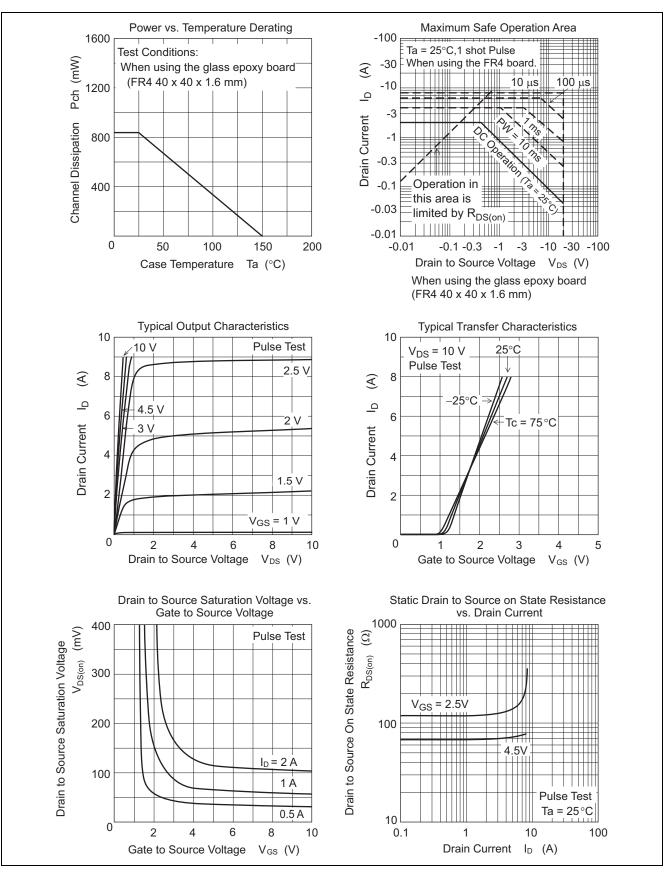
Electrical Characteristics

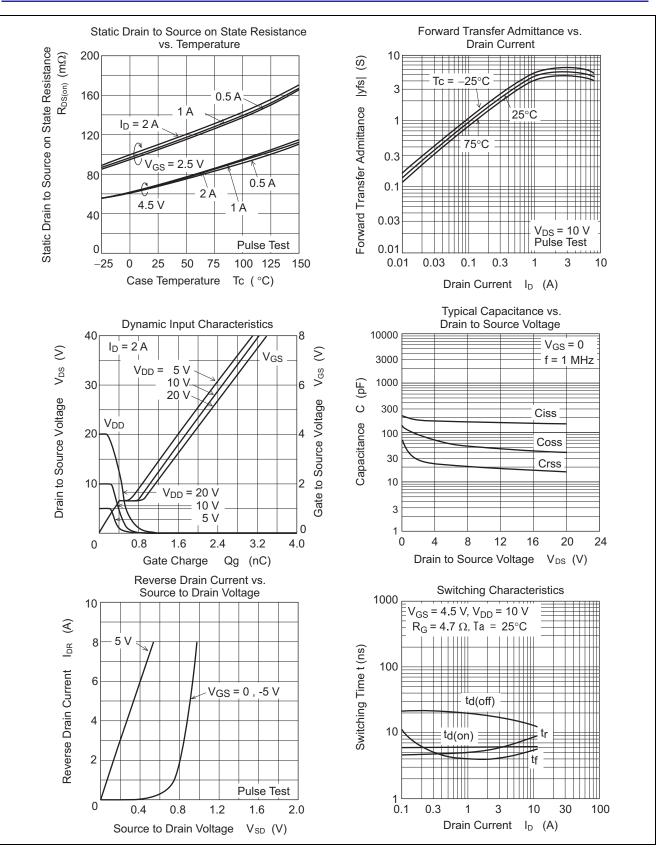
						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to Source breakdown voltage	V _{(BR)DSS}	20	_	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to Source breakdown voltage	V _{(BR)GSS}	±12	—	—	V	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to Source leak current	I _{GSS}	_	—	±10	μA	$V_{GS} = \pm 10$ V, $V_{DS} = 0$
Drain to Source leak current	I _{DSS}	_	—	1	μA	$V_{DS} = 20 V, V_{GS} = 0$
Gate to Source cutoff voltage	V _{GS(off)}	0.4	—	1.4	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Drain to Source on state resistance	R _{DS(on)}	_	69	90	mΩ	$I_D = 1 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note3}}$
	R _{DS(on)}	_	107	150	mΩ	$I_D = 1 \text{ A}, V_{GS} = 2.5 \text{ V}^{\text{Note3}}$
Forward transfer admittance	yfs	3	4.5	_	S	$I_D = 1 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note3}}$
Input capacitance	Ciss	_	165	_	pF	V _{DS} = 10 V
Output capacitance	Coss	_	50	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	20	—	pF	f = 1 MHz
Turn - on delay time	t _{d(on)}	_	6	—	ns	I _D = 1 A
Rise time	tr	_	5	—	ns	V _{GS} = 10 V
Turn - off delay time	t _{d(off)}	_	20	—	ns	$R_L = 10 \Omega$
Fall time	t _f	_	4	—	ns	Rg = 4.7 Ω
Total Gate charge	Qg		1.8		nC	V _{DD} = 10 V
Gate to Source charge	Qgs	_	0.4	_	nC	V _{GS} = 4.5 V
Gate to Drain charge	Qgd	_	0.4	_	nC	$I_D = 2 A$
Body - Drain diode forward voltage	V _{DF}	—	0.8	1.1	V	$I_F = 2 A, V_{GS} = 0^{Note3}$

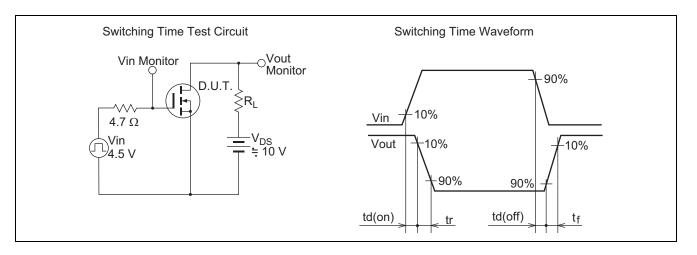
Notes: 3. Pulse test



Main Characteristics

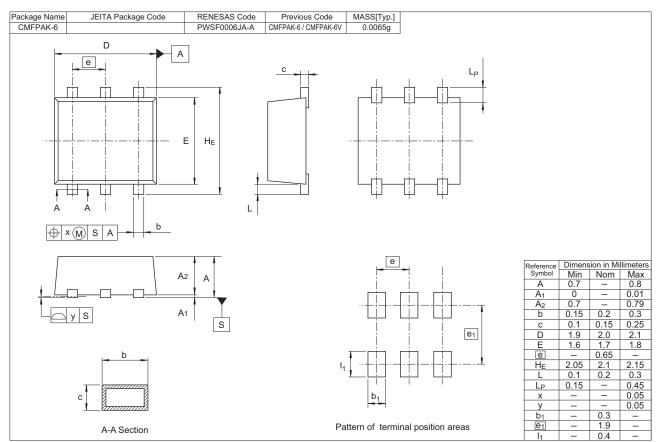








Package Dimensions



Ordering Information

Orderable Part Number	Quantity	Shipping Container		
HAT2203C-EL-E	3000 pcs	Taping		



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